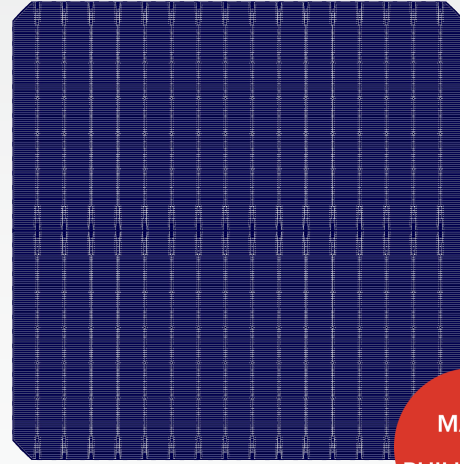
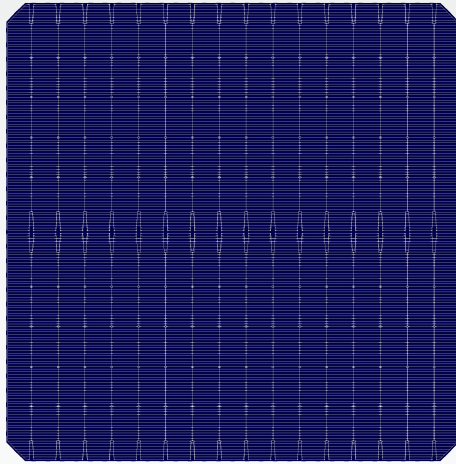


M182.2-N TYPE 16BB Data Sheet



MADE
IN
PHILIPPINES



High conversion efficiency with high reliability



No light-induced degradation



Uniform cell performance with stable process control



Both sides can generate electricity



Low mismatch of cell performance during encapsulation



Excellent power generation performance under low irradiation



Low hot spot effect

SOLARIS
PANABO

M182.2-N TYPE 16BB Data Sheet

TECHNICAL CHARACTERISTICS

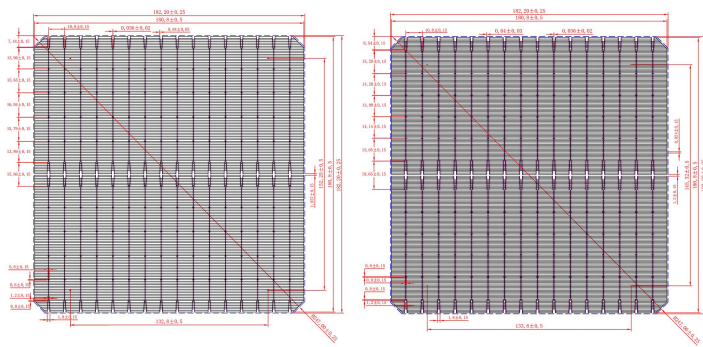
Dimension	182.2mm*182.2mm±0.25mm	TkVoltage:-(0.27±0.03) %/K
Thickness	130um±13um	TkCurrent:+(0.045±0.015) %/K
Front	16 bus bars, 172 lines, Silicon oxide + blue silicon nitride compound anti reflection coating	TkPower:-(0.33±0.02) %/K
Back(+)	16 bus bars, 220 lines, Silicon oxide + blue silicon nitride compound anti reflection coating	Rsh≥50Ω,Irev2≤0.5A

LIGHT INTENSITY AND RELIABILITY

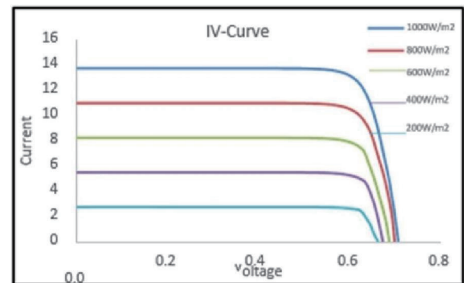
Intensity(W/m ²)	Uoc	Isc
1000	1.000	1.000
900	0.996	0.903
800	0.991	0.803
600	0.988	0.602
400	0.962	0.403

Using Xenon lamp (Irradiance of 1000W/m², with spectrum AM 1.5) to irradiate test cells, after a total irradiation of 5 kwh/m², the degradation of maximum output power of cells is 2%

PRINTING GRAPHICS



IV CURVE



WELDABILITY

Minimum peeling intensity ≥1.0N/mm

Results may vary depending on the welding ribbon, welding methods and conditions.

FRONT SIDE ELECTRICAL PERFORMANCE

Eff(%)	Pmp(W)	Vmpp(V)	Impp(A)	Voc(V)	ISC(A)
25.0	8.25	0.622	13.305	0.724	13.699
24.9	8.22	0.621	13.267	0.723	13.666
24.8	8.19	0.620	13.223	0.722	13.622
24.7	8.15	0.619	13.180	0.721	13.581
24.6	8.12	0.618	13.147	0.720	13.548
24.5	8.09	0.617	13.112	0.719	13.516
24.4	8.05	0.616	13.068	0.718	13.481
24.3	8.02	0.615	13.045	0.717	13.466
24.2	7.99	0.614	13.012	0.716	13.442
24.1	7.96	0.613	12.980	0.715	13.419
24.0	7.92	0.612	12.947	0.714	13.395
23.9	7.89	0.611	12.914	0.713	13.370
23.8	7.86	0.610	12.881	0.712	13.346
23.7	7.82	0.609	12.848	0.711	13.322
23.6	7.79	0.608	12.815	0.710	13.297

STC:1000W/m²,AM1.5,25 C